

GSM6911P

60V P-Channel MOSFETs

Product Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

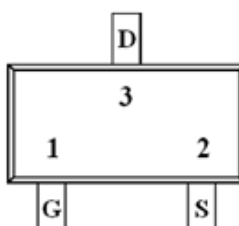
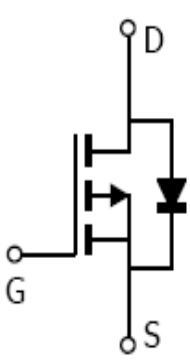
Features

- -60V, -3.1A, $R_{DS(ON)}=190m\Omega@V_{GS}=-10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available
- SOT-23 package design

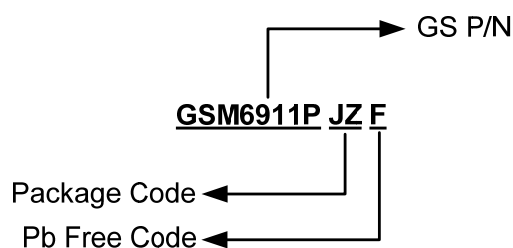
Applications

- Motor Drive
- Power Tools
- LED Lighting

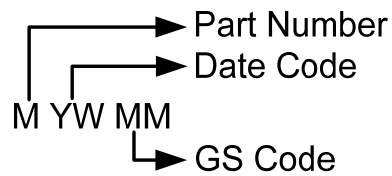
Packages & Pin Assignments

GSM6911PJZF (SOT-23)	
 <p>Top Views</p>	
	
Pin	Description
1	Gate
2	Source
3	Drain

Ordering Information



Marking Information



Part Number	Package	Part Marking	Quantity
GSM6911PJZF	SOT-23	MYWMM	3000pcs

Absolute Maximum Ratings

T_A=25°C Unless otherwise noted

Symbol	Parameter	Typical	Unit
V _{DS}	Drain-Source Voltage	-60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	T _A =25°C	-3.1
		T _A =100°C	-2
I _{DM}	Pulsed Drain Current	-12.4	A
EAS	Single Pulse Avalanche Energy	32	mJ
IAS	Single Pulse Avalanche Current	-8	A
P _D	Power Dissipation (T _A =25°C)	1.56	W
	Power Dissipation (Derate above 25°C)	0.012	W/°C
T _J	Operating Junction Temperature Range	-50 to +150	°C
T _{STG}	Storage Temperature Range	-50 to +150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient	80	°C/W

Electrical Characteristics

T_A=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-60			V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA		-0.05		V/°C
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1.2	-1.9	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient			5		mV/°C
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-60V, V _{GS} =0V			-1	uA
		V _{DS} =-48V, V _{GS} =0V, T _J =125°C			-10	
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			-3.1	A
I _{SM}	Pulsed Source Current				-12.4	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =-10V, I _D =-3A		160	190	mΩ
		V _{GS} =-4.5V, I _D =-1.5A		200	240	
g _{FS}	Forward Transconductance	V _{DS} =-10V, I _D =-3A		3.5		S
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A			-1	V
Dynamic						
Q _g	Total Gate Charge	V _{DS} =-30V, V _{GS} =-10V, I _D =-3A		8.2	12	nC
Q _{gs}	Gate-Source Charge			1.8	3.6	
Q _{gd}	Gate-Drain Charge			1.5	3	
C _{iss}	Input Capacitance	V _{DS} =-30V, V _{GS} =0V, f=1MHz		425	615	pF
C _{oss}	Output Capacitance			35	50	
C _{rss}	Reverse Transfer Capacitance			20	30	
t _{d(on)}	Turn-On Time	V _{DD} =-30V, I _D =-1A, V _{GS} =-10V, R _G =6Ω		5.2	10	ns
t _r				19	36	
t _{d(off)}	Turn-Off Time			35	67	
t _f				10.6	20	

Typical Performance Characteristics

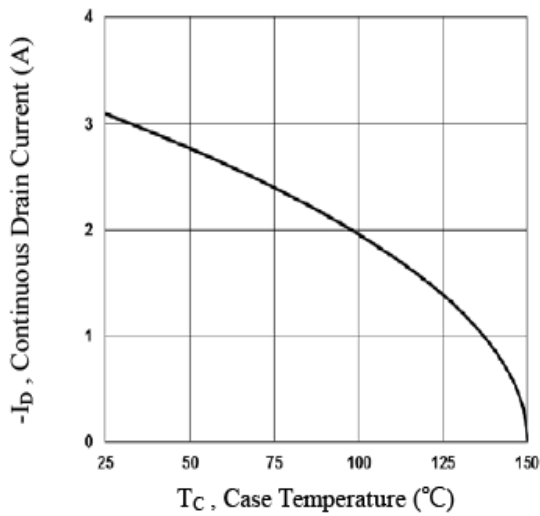


Fig.1 Continuous Drain Current vs. T_c

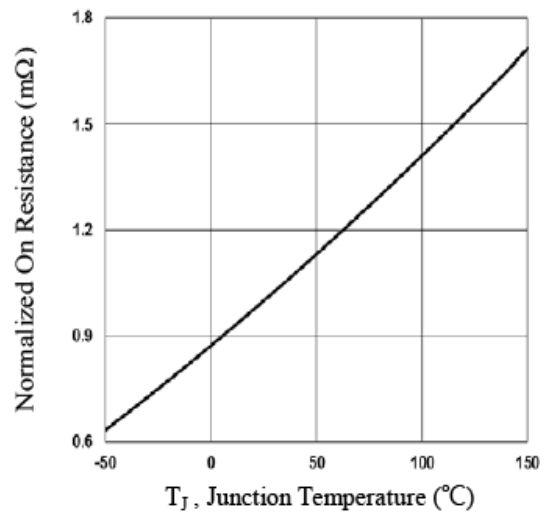


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

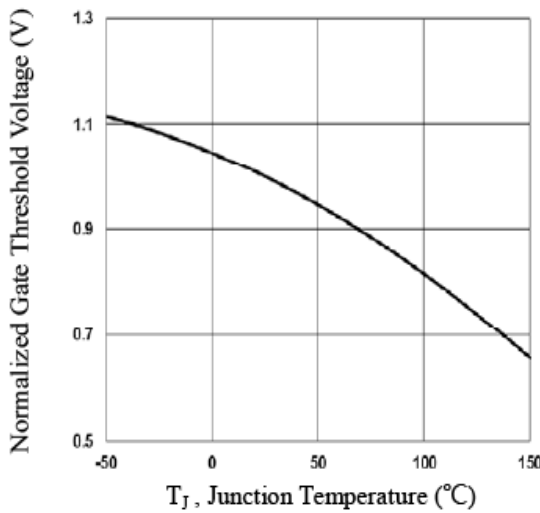


Fig.3 Normalized V_{th} vs. T_j

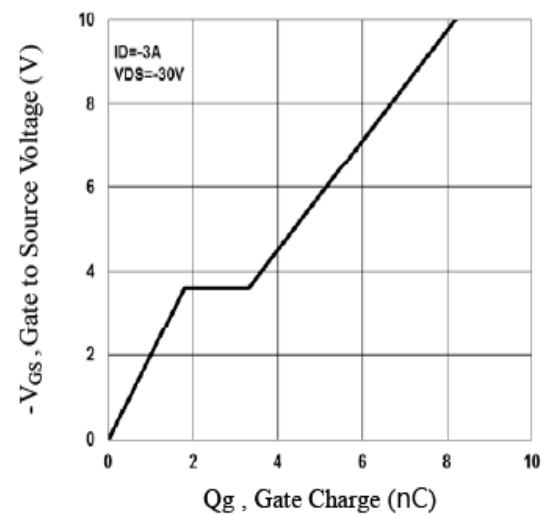


Fig.4 Gate Charge Waveform

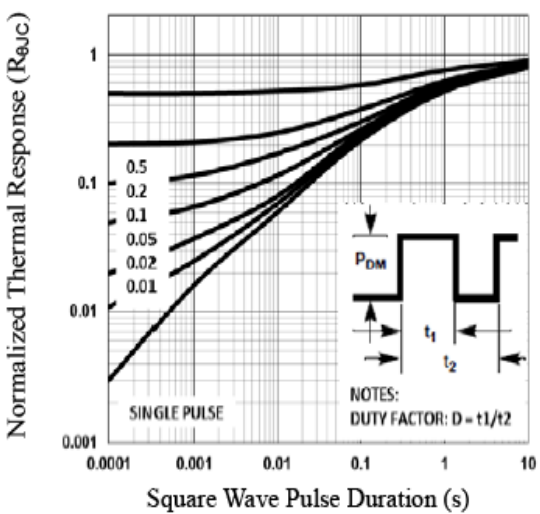


Fig.5 Normalized Transient Impedance

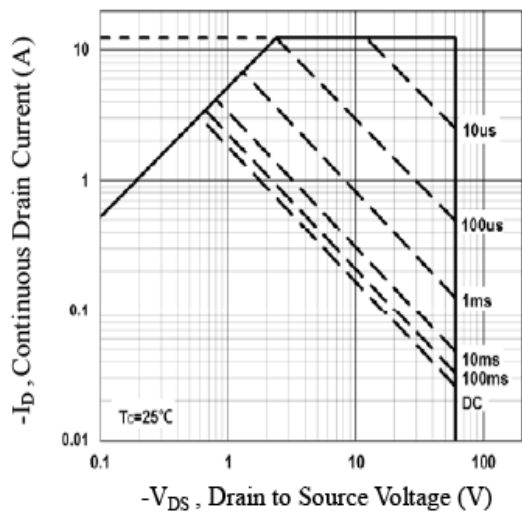
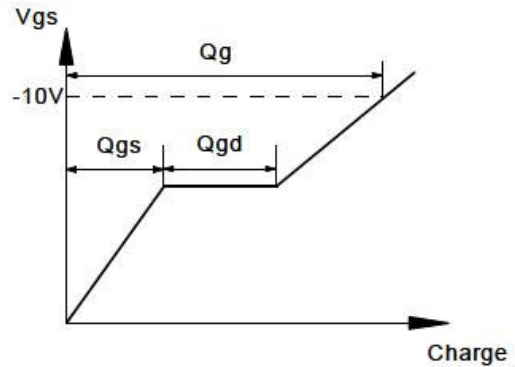
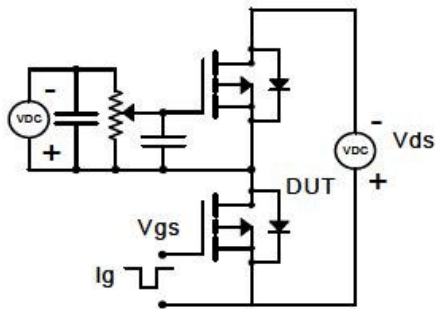


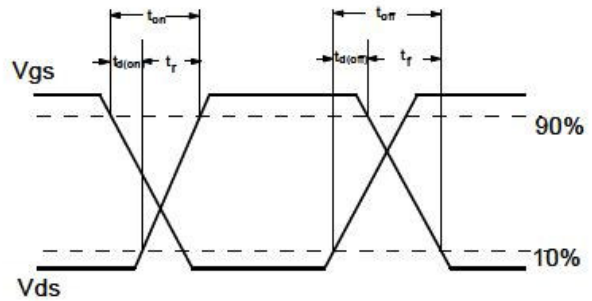
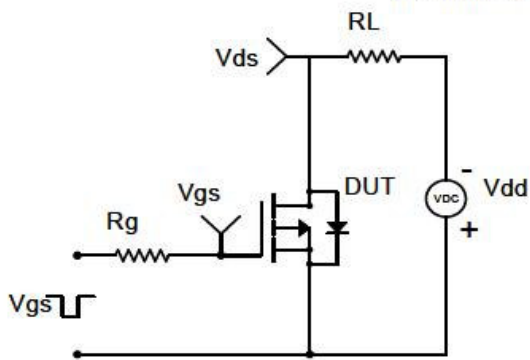
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

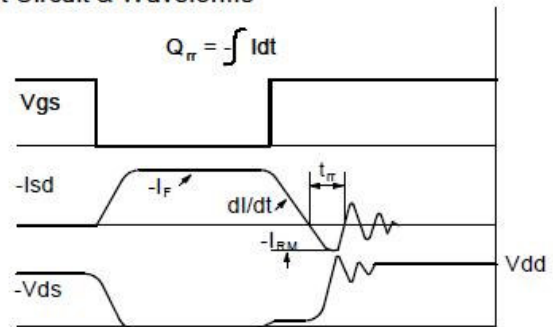
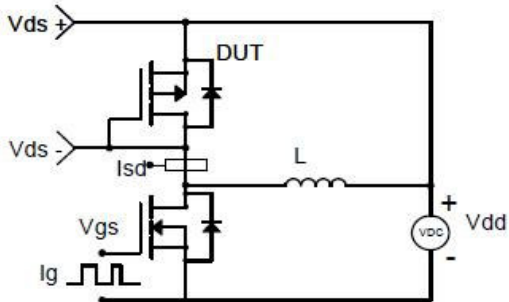
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

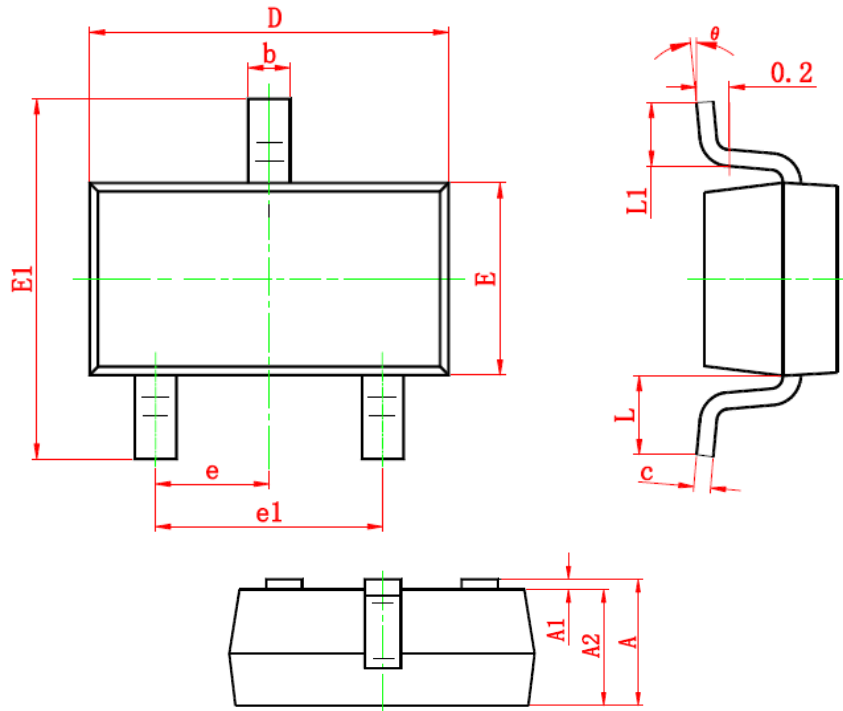


Diode Recovery Test Circuit & Waveforms



Package Dimension

SOT-23










Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°



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